# UNISONIC TECHNOLOGIES CO., LTD

**JFET** 

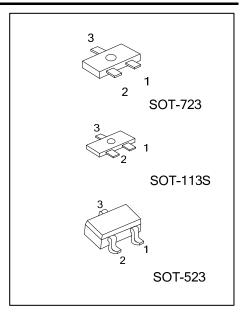
# **CAPACITOR MICROPHONE APPLICATIONS**

#### **DESCRIPTION**

The UTC TF212 uses advanced trench technology to provide excellent R<sub>DS (ON)</sub>, low gate charge and operation with low gate voltages. This device is suitable for use in capacitor microphone applications.

#### **FEATURES**

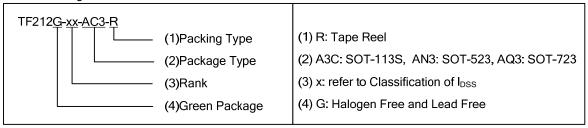
- \* Suited for use in audio, telephone capacitor microphones.
- \* Good voltage characteristic.
- \* Good transient characteristic.



#### ORDERING INFORMATION

Ordering Number	Package	Pin Assignment			Dooking	
Ordering Number		1	2	3	Packing	
TF212G-xx-A3C-R	SOT-113S	S	D	G	Tape Reel	
TF212G-xx-AN3-R	SOT-523	S	D	G	Tape Reel	
TF212G-xx-AQ3-R	SOT-723	S	D	G	Tape Reel	

Note: Pin Assignment: S: Source D: Drain G: Gate



#### **MARKING**

TF212-F4	TF212-F5	
F4	F5	

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## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Gate Drain Voltage	$V_{GDO}$	-20	V
Gate Current	I <sub>G</sub>	10	mA
Drain Current	I <sub>D</sub>	1	mA
Power Dissipation	P <sub>D</sub>	100	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

# ■ ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C, unless otherwise specified)

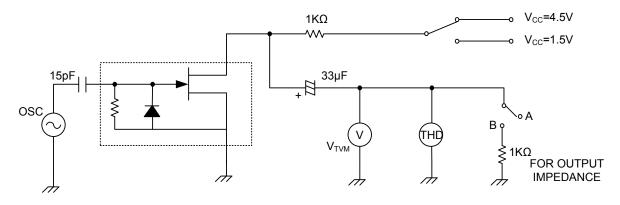
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Gate Drain Breakdown Voltage	$BV_GDO$	I <sub>G</sub> =-100μA	-20			V
Gate Source Cut off Voltage	$V_{\text{GS}(\text{OFF})}$	$V_{DS}$ =5 $V$ , $I_D$ =1 $\mu$ A	-0.2	-0.6	-1.2	V
Drain Current	$I_{DSS}$	V <sub>DS</sub> =5V, V <sub>GS</sub> =0	140		350	μA
Forward Transfer Admittance	IYFSI	V <sub>DS</sub> =2V, V <sub>GS</sub> =0, f=1KHz	1	1.2		mS
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0, f=1MHz		3.5		pF
Output Capacitance	C <sub>RSS</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0, f=1MHz		0.65		рF
Voltage Gain	Gv	V <sub>IN</sub> =10mV, f=1KHz		-3		dB
Reduced Voltage Characteristic	$\triangle G_{VV}$	V <sub>IN</sub> =10mV,f=1KHz, V <sub>CC</sub> =4.5V→1.5V		-1.2	-3.5	dB
Frequency Characteristic	$\triangle G_{Vf}$	f=1KHz to 110Hz			-1	dB
Input Resistance	$Z_{IN}$	f=1KHz	25			МΩ
Output Resistance	Zo	f=1KHz			700	Ω
Total Harmonic distortion	THD	V <sub>IN</sub> =30mV, f=1KHz		1		%
Output Noise Voltage	$V_{NO}$	V <sub>IN</sub> =0			-110	dB

# ■ CLASSIFICATION OF I<sub>DSS</sub>

RANK	F4	F5
RANGE	140-240	210-350

TF212 JFET

## ■ TEST CIRCUIT (T<sub>A</sub>=25°C)



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